AVD075P

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AVD075P** is designed for applications requiring Class C, High Peak Power and low duty cycle such as IFF, DME and TACAN

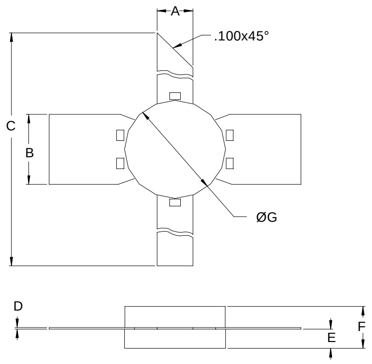
FEATURES:

- Internal Input Matching Network
- **P_G** = 7.5 dB at 75 W/1150 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	5.5 A PEAK
V_{CB}	65 V
P_{DISS}	220 W PEAK
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.8 °C/W

PACKAGE STYLE .280 4L PILL (A)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	.195 / 4.95	.205 / 5.21
C	1.000 / 25.40	
D	.004 / 0.10	.007 / 0.18
E	.050 / 1.27	.065 / 1.65
F		.145 / 3.68
G	.275 / 6.99	.285 / 7.21

ORDER CODE: ASI10561

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 10$ mA	65			**V**
BV_{CER}	$I_C = 10$ mA $R_{BE} = 10\ \Omega$	65			**V**
BV_{EBO}	$I_E = 1$ mA	3.5			**V**
I_{CES}	$V_{CE} = 50$ V			5.0	**mA**
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	11		200	**---**
P_G **η_C**	$V_{CC} = 50$ V $P_{OUT} = 75$ W f = 1025 - 1150 MHz $P_{IN} = 13.5$ W	7.5 35			**dB** **%**

NOTE: Pulse Width = 10 µS Duty Cycle = 1 %